

An article entitled "Anisotropy of electrical and optical properties in B-Ga₂O₃ single crystals" from Appl. Phys. Lett. 71(7), N. Ueda et al., pp. 933-935 (Aug. 18, 1997).
 An article entitled "Synthesis and control of conductivity of ultraviolet transmitting B-Ga₂O₃ single crystals" from Appl. Phys. Lett. 70(26), N. Ueda, pp. 3561-3563 (Jun. 30, 1997).

Primary Examiner:
 Attorney, Agent or Firm:

Figures

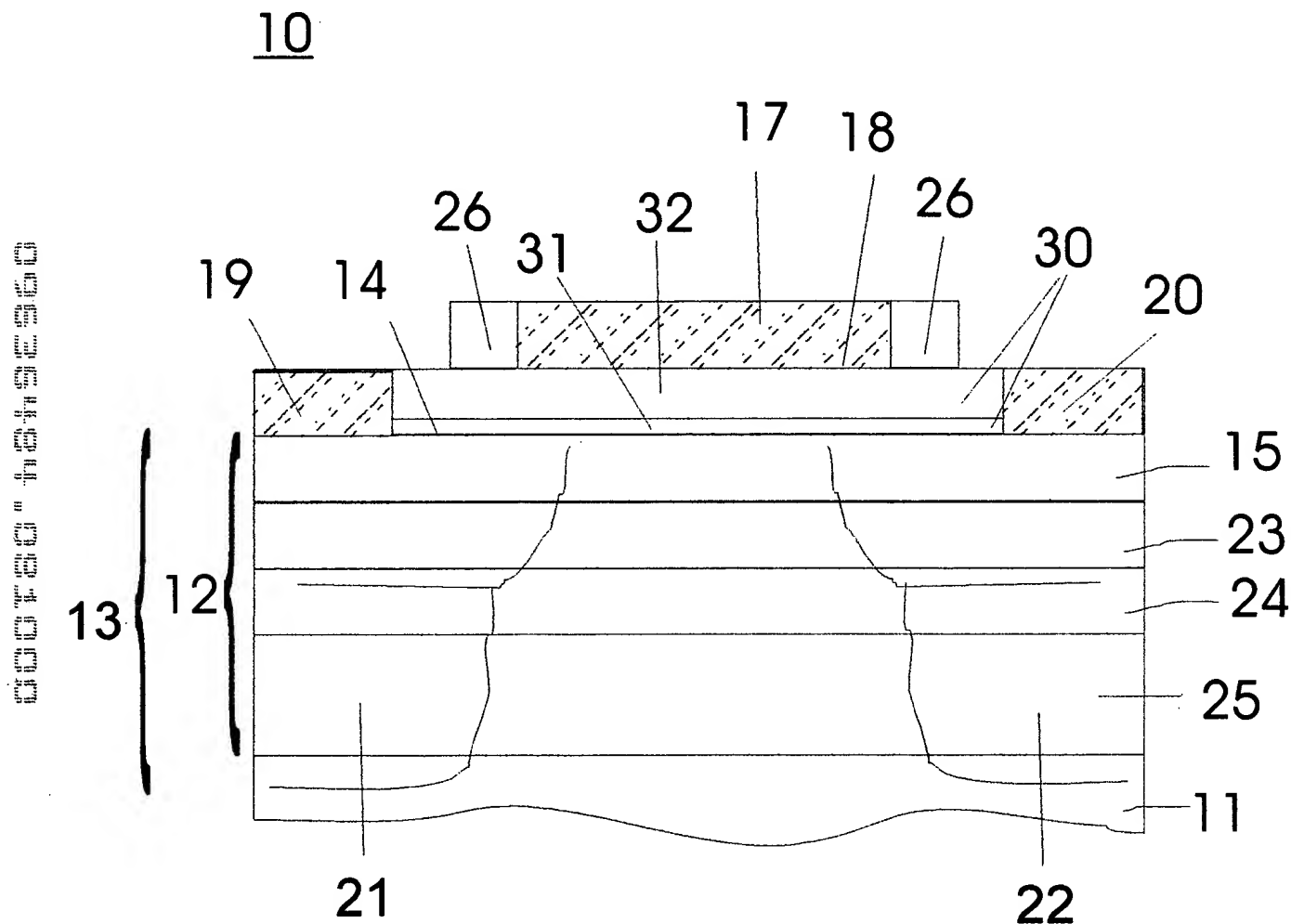


Figure 1

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graph TD; 100[Provide Compound Semiconductor Substrate] --> 102[Deposit Compound Semiconductor Epitaxial Structure]; 102 --> 103[Transfer Compound Semiconductor Structure to Insulator Deposition Chamber]; 103 --> 104[Deposit layer of Gallium Oxygen Compounds on upper Surface of Compound Semiconductor Structure]; 104 --> 105[Deposit Layer of Gallium Oxygen and at least one Rare Earth Element onto Upper Surface of Gallium Oxygen Layer]; 105 --> 106[Position Stable Refractory Metal on Gate Oxide Insulator Layer Structure]; 106 --> 108[Provide Source and Drain Implant Regions that are Self-Aligned to Gate Electrode]; 108 --> 110[Position Source and Drain Ohmic Contacts]; 110 --> 112[Provide Interconnection Means for the Formation of an Integrated Circuit];
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100 Provide Compound Semiconductor Substrate

102 Deposit Compound Semiconductor Epitaxial Structure

103 Transfer Compound Semiconductor Structure to Insulator Deposition Chamber

104 Deposit layer of Gallium Oxygen Compounds on upper Surface of Compound Semiconductor Structure

105 Deposit Layer of Gallium Oxygen and at least one Rare Earth Element onto Upper Surface of Gallium Oxygen Layer

106 Position Stable Refractory Metal on Gate Oxide Insulator Layer Structure

108 Provide Source and Drain Implant Regions that are Self-Aligned to Gate Electrode

110 Position Source and Drain Ohmic Contacts

112 Provide Interconnection Means for the Formation of an Integrated Circuit

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